V-Cell Mono Series

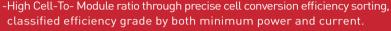
TSS65TN

6" Mono c-Si Solar Cell









- -Excellent electrical long-term stability and reliability by using of best raw materials and through strict quality inspection control.
- -Low breakage rate by using high qualified and stable wafers.
- -High quality homogeneous appearance by sorting into defined color classes.
- -100% screened for reverse current and shunt resistance.
- -Excellent passivation quality of the rear side compared to the traditional solar cell is clearly visible in the long wavelength regime.
- -The best solution for PV module with above 280W outputs.

Quality Control and Professional Service

- -Regular calibration of test equipment using Fraunhofer ISE reference cell.
- -Environmental friendly due to REACH-SVHC and RoHS compliances.
- -Professional on-site service and support for module certification.
- -Regular light source AAA class calibration for stable conversion efficiency.
- -Lowest LID by periodic monitoring and superior wafer incoming control.

Physical Characteristics

Dimensions 156.75mm X 156.75 mm ± 0.25mm

Diagonal: 210mm

Thickness(Si) $180 \mu \text{m} \pm 20 \mu \text{m}$, $200 \mu \text{m} \pm 30 \mu \text{m}$

Front(-) Alkaline texturized surface with silicon nitride anti-reflecting coating

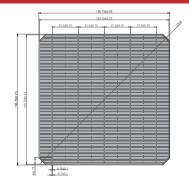
Color: Dark Blue, Blue, Sky Blue
5 X 0.7 mm ± 0.1 mm wide bus bars

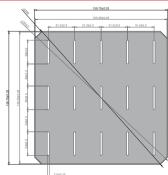
Distance between bus bars : 31.2 mm

Back(+) Aluminum back surface field

5x3 soldering pads, 2.0 mm ± 0.15 mm wide bus bars

Distance between bus bars: 31.2 mm





Electrical Characteristics

Efficiency Code		219	218	217	216	215	214	213	212	211	210	209
Efficiency	Eff(%)	21.90	21.80	21.70	21.60	21.50	21.40	21.30	21.20	21.10	21.00	20.90
Power	Pmpp(W)	5.35	5.33	5.30	5.28	5.25	5.23	5.20	5.18	5.16	5.13	5.11
Max. Power Current	Impp(A)	9.256	9.250	9.227	9.211	9.196	9.180	9.165	9.149	9.134	9.121	9.112
Short Circuit Current	Isc(A)	9.771	9.758	9.736	9.722	9.708	9.695	9.678	9.660	9.645	9.634	9.627
Max. Power Voltage	Vmpp(V)	0.578	0.576	0.575	0.573	0.571	0.570	0.568	0.566	0.564	0.563	0.560
Open Circuit Voltage	Voc(V)	0.678	0.675	0.674	0.673	0.671	0.669	0.667	0.665	0.664	0.662	0.661

Standard test condition: AM1.5, 1000W/m², 25°c Average accuracy of all tests is +/-1.5% rel.

TSS65TN 6" Mono c-Si Solar Cell

Temperature Coefficients

Current Temperature Coefficient a (IS	0.043%/K
Voltage Temperature Coefficient B (VC	-0.30 %/K
Power Temperature Coefficient Y(Pro	-0.38 %/K

Standard test condition: AM1.5, 1000W/m2, 25°c

Processing Recommendations

Solder Joint

Copper ribbons coated with $15\sim25\mu m$: 62%Sn/36%Pb/2%Aq or 60%Sn/40%Pb

Standard test condition: AM1.5, 1000W/m2, 25°c

Solderability

Peel Strength Minimum

>1.25 N/mm

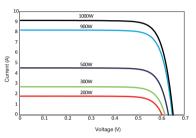
Soldering results may differ due to different flux, ribbons, soldering methods, and parameters.

Qualifications and Certificates

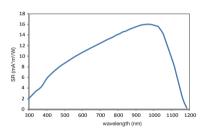


RoHS Compliance SVHC tested

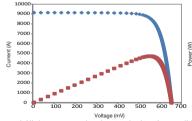
Typical Current-Voltage Curve



Typical Spectral Response

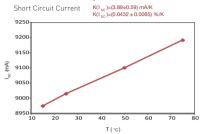


Typical IV-Power Curve

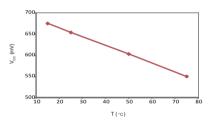


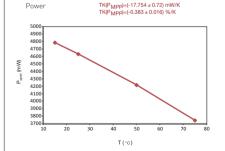
- * All data measured under standard testing condition (STC): 1000 W/m², AM 1.5, 25 °C.
- * All figures bear ±2% tolerance.
- * Reference cell calibrated by the Fraunhofer ISE in Freiburg.

Calculated Temperature Coefficients



Open Circuit Voltage TK (Voc)=(-1.980 ± 0.039) mV / K TK (Voc)=(-0.303 ± 0.0059) % / K





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D210_M

Specifications are subject to change without prior notice.
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